

 UMC

UM23C128-A/-B

16,384× 8-BIT CMOS MASK-PROGRAMMABLE ROM

Features

- 16,384 × 8-bit organization
- Single +5V power supply
- Access time: 150 ns (max.)
- Current: Operating: 30 mA (max.)
Standby: 30 µA (max.)
- Mask Programmed for chip enable (powerdown) CE/CĒ

and chip select CS/CS̄

- 3-state outputs for wired-OR expansion
- Fully static operation
- TTL-compatible inputs and outputs
- Available in 28 pin DIP packages (UM23C128-A/B) or in chip form (UM23C128H-A/B)

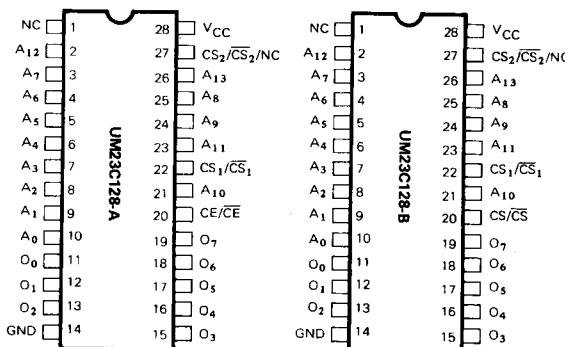
General Description

The UM23C128-A/B is a high performance Read Only Memory organized 16,384 words by 8 bits with an access time of 150 ns. It is designed to be compatible with all microprocessors and similar applications where high-performance large-bit storage and simple interfacing are important design considerations.

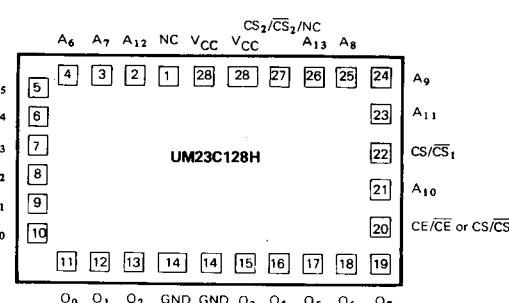
The UM23C128-A offers automatic powerdown with powerdown controlled by the Chip Enable CE/CĒ input.

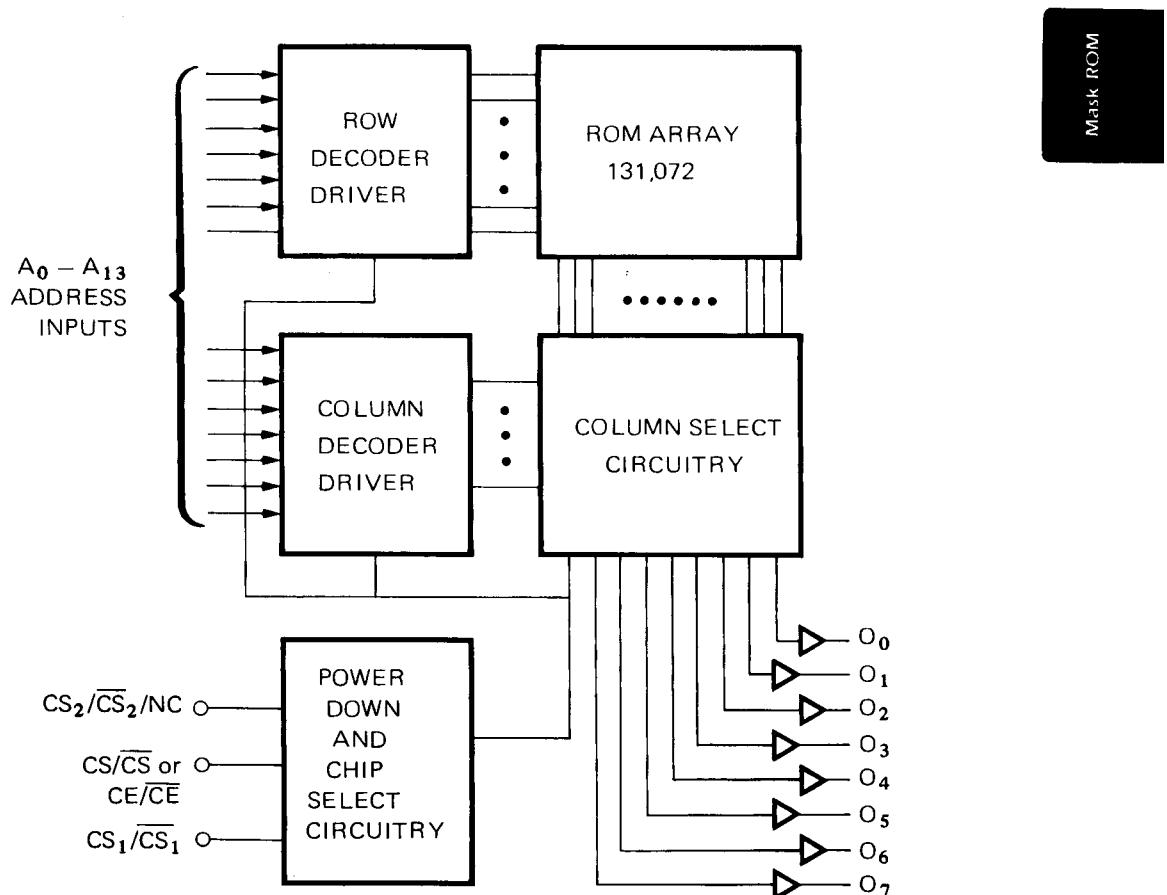
When CE/CĒ goes LOW/HIGH, the device will automatically power down and remain in a low power standby mode as long as CE/CĒ remains LOW/HIGH. This unique feature provides system level power savings of as much as 99%. The functions of Pin 22 and Pin 27 are CS₁/CS̄₁ and CS₂/CS̄₂/NC, respectively. For UM23C128-B, Pin 20 may also be programmed as CS/CS̄ (active HIGH or LOW) in order to eliminate bus contention in multiple bus microprocessor systems.

Pin Configurations



Pad Configuration



Block Diagram




UM23C128-A/-B

Pin Description

Pin No.	Symbol	Description
2-10, 21, 23-26	A ₀ -A ₁₃	Address Input
11-13, 15-19	O ₀ -O ₇	Data Output
14	GND	Ground
28	V _{CC}	Power Supply
20 -A	CE/CĒ	Chip Enable Input
-B	CS/CS̄	Chip Select Input
22	CS ₁ /CS̄ ₁	Chip Select Input
27	CS ₂ /CS̄ ₂ /NC	Chip Select or No Connection

Recommended DC Operating Conditions

(T_A = 0°C to +70°C)

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{CC}	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V _{IH}	Input High Voltage	2.2		V _{CC} + 0.3	V
V _{IL}	Input Low Voltage	-0.5		0.8	V

Absolute Maximum Ratings*

Ambient Operating Temperature	−10 to +80°C
Storage Temperature	−65 to +150°C
Supply Voltage to Ground Potential	−0.5 to 7.0V
Output Voltage	−0.5 to V _{CC} + 0.5V
Input Voltage	−0.5 to V _{CC} + 0.5V
Power Dissipation	400 mW

*Comments

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied and exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC Electrical Characteristics (T_A = 0°C to +70°C, V_{CC} = 5.0V ± 10%, GND = 0V)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
V _{OH}	Output HIGH Voltage	2.4		V _{CC}	V	I _{OH} = −1 mA	
V _{OL}	Output LOW Voltage			0.4	V	I _{OL} = 3.2 mA	
V _{IH}	Input HIGH Voltage	2.2		V _{CC} + 0.3	V		
V _{IL}	Input LOW Voltage	−0.5		0.8	V		
I _{LH}	Input Leakage Current			10	μA	V _{IN} = 0V to V _{CC}	
I _{LO}	Output Leakage Current			10	μA	V _{OUT} = 0V to V _{CC}	
I _{CC}	Operating Supply Current		10	30	mA		1
I _{SB}	Standby Supply Current		0.2	1.5	mA	CĒ = V _{IH} , CE = V _{IL}	
I _{SB1}	Standby Supply Current		10	30	μA	CĒ = V _{CC} − 0.2V, CE = 0.2V	
I _{OS}	Output Short Circuit Current			70	mA		2

Capacitance:

Symbol	Parameter	Min.	Max.	Unit	Test Conditions	Note
C _I	Input Capacitance		10	pF	T _A = 25°C	
C _O	Output Capacitance		10	pF	f = 1.0 MHz	3

AC Characteristics ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, $V_{CC} = 5.0\text{V} \pm 10\%$, $\text{GND} = 0\text{V}$)

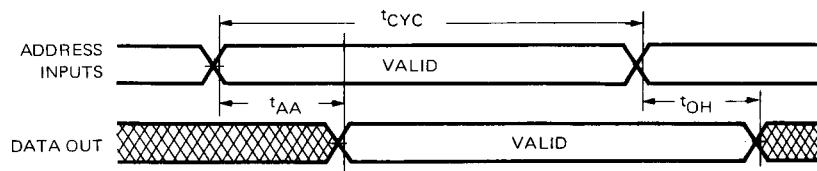
Symbol	Parameter	Min.	Max.	Unit	Note
t_{CYC}	Cycle Time	150		ns	
t_{AA}	Address Access Time		150	ns	
t_{ACE}	Chip Enable Access Time		150	ns	
t_{ACS}	Chip Select Access Time		70	ns	
t_{OH}	Output Hold After Address Change	10		ns	
t_{LZ}	Output Low Z Delay	10		ns	4
t_{HZ}	Output High Z Delay		70	ns	5
t_{PU}	Power-Up Time	0		ns	
t_{PD}	Power-Down Time		85	ns	

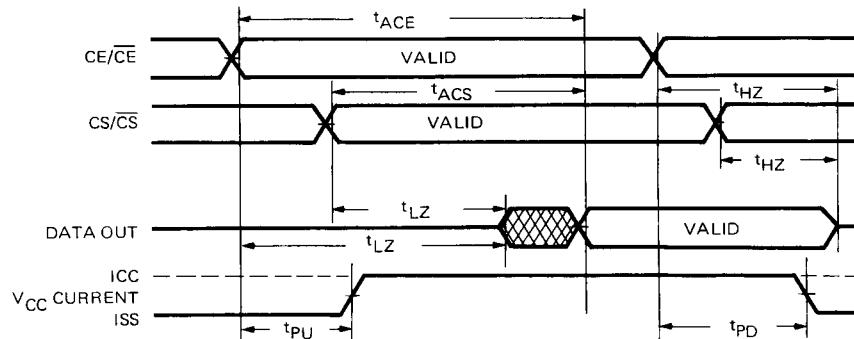
Notes:

1. Measured with device selected and output unloaded.
2. For a duration not to exceed 30 seconds.
3. This parameter is periodically sampled and is not 100% tested. All pins except for pins under test are tied to ground.
4. Output LOW impedance delay (t_{LZ}) is measured from the later of $\text{CE}/\overline{\text{CE}}$ or $\text{CS}/\overline{\text{CS}}$ going active.
5. Output HIGH impedance delay (t_{HZ}) is measured from the earlier of $\text{CE}/\overline{\text{CE}}$ or $\text{CS}/\overline{\text{CS}}$ going inactive.

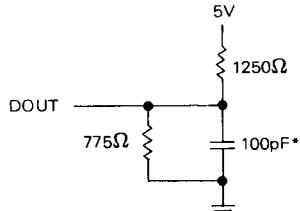
Timing Waveforms

PROPAGATION DELAY FROM ADDRESS (CE/ $\overline{\text{CE}}$ = ACTIVE, CS/ $\overline{\text{CS}}$ = ACTIVE)



PROPAGATION DELAY FROM CHIP ENABLE, OR CHIP SELECT (ADDRESS VALID)

AC Test Conditions

Input Pulse Levels	0.4 ~ 2.4V
Input Rise And Fall Times	10 ns
Timing Measurement Reference Level	$V_{IL} = 0.8V$ $V_{IH} = 2.2V$ $V_{OL} = 0.8V$ $V_{OH} = 2.0V$
Output Load	See Figure 1



*INCLUDING SCOPE AND JIG

Figure 1 Output Load Circuit

Functions
Truth Table (UM23C128-A)

CE	CS ₁	CS ₂	O ₀ – O ₇	Mode
I	X	X	HI-Z	Power Down
A	I	X	HI-Z	Output Disable
A	X	I	HI-Z	Output Disable
A	A	A	Output Data	Read

Truth Table (UM23C128-B)

CS	CS ₁	CS ₂	O ₀ – O ₇	Mode
I	X	X	HI-Z	Output Disable
X	I	X	HI-Z	Output Disable
X	X	I	HI-Z	Output Disable
A	A	A	Output Data	Read

Read Mode

1. Data can be read in case of setting address, CS₁ = A, CS₂ = A, CE = A (UM23C128-A) and CS = A, CS₁ = A, CS₂ = A (UM23C128-B).
2. CS₂/CS₁/NC, CS₁/CS₂, CE/CĒ are mask programmable which can be selected for either active level. When ordering, please specify -A or -B and the active level CS/CS̄/NC, CE/CĒ/CS/CS̄.
3. "A" means "Active".
"I" means "Inactive".
"X" means "Active" or "Inactive".
4. If Pin 27 is set to no-connection, the Input level will be internally fixed at active level.



UM23C128-A/-B

Ordering Information

Part No.	Access Time (ns)	Operating Current Max. (mA)	Standby Current Max. (mA)	Package	Power Down
UM23C128-A	150	30	0.03	28L DIP	YES
UM23C128H-A				Chip Form	YES
UM23C128-B	150	30	0.03	28L DIP	NO
UM23C128H-B				Chip Form	NO

Mask ROM